

Appendix II

Gallium ion sputter yield on silicon substrate⁹

Energy (keV) Angle (°)	5	10	20	30
0	1.23	2.12	2.15	2.12
5	1.65	1.94	2.13	2.25
10	1.73	2.22	2.70	2.21
15	1.23	2.13	2.18	2.19
20	1.55	2.22	1.95	2.44
25	1.30	2.06	2.13	2.85
30	2.05	2.54	2.87	3.24
35	2.25	3.14	3.60	3.39
40	2.60	4.11	4.40	3.69
45	4.10	4.70	5.80	5.04
50	4.73	5.34	7.55	5.51
55	5.38	5.58	7.57	6.47
60	5.65	7.47	8.93	8.78
65	8.13	9.40	10.43	10.80
70	8.65	10.44	12.40	12.75
75	8.40	11.50	14.13	14.62
78	9.50	12.10	17.10	16.37
80	7.35	12.24	15.98	16.83
82	7.75	10.86	14.93	16.96
84	4.88	8.95	14.09	16.24
86	3.28	6.46	10.60	13.22
88	0.20	1.19	2.97	1.82
89	0.08	0.14	0.22	0.36

⁹ The sputter yield in this form is calculated by TRIDYN.

Gallium ion sputter yield on diamond substrate¹⁰

Energy (keV) Angle (°)	5	10	20	30
0	0.86	1.03	1.14	1.26
5	0.87	1.08	1.21	1.27
10	0.90	1.11	1.04	1.35
15	0.97	1.27	1.40	1.48
20	1.09	1.32	1.42	1.60
25	1.24	1.51	1.72	1.72
30	1.42	1.74	1.95	2.04
35	1.64	2.02	2.23	2.31
40	1.99	2.39	2.67	2.75
45	2.35	2.88	3.12	3.24
50	2.77	3.40	3.43	3.77
55	3.39	4.02	4.47	4.61
60	4.22	5.00	4.51	5.66
65	5.32	6.30	6.94	7.10
70	6.52	7.87	8.59	9.08
75	7.76	9.92	11.59	12.11
78	8.14	11.24	12.11	14.16
80	7.95	11.26	12.68	15.67
82	7.10	10.83	12.47	16.06
84	5.16	8.77	13.29	16.06
86	2.21	4.69	6.51	8.23
88	0.36	0.59	0.7	2.79
89	0.09	0.07	0.04	0.10

¹⁰ The sputter yield in this form is calculated by TRIDYN.